

Title (en)

INSTALLATION AND METHOD FOR REDUCING THE CONTENT IN ELEMENTS, SUCH AS BORON, OF HALOSILANES

Title (de)

ANLAGE UND VERFAHREN ZUR VERMINDERUNG DES GEHALTES VON ELEMENTEN, WIE BOR, IN HALOGENSILANEN

Title (fr)

INSTALLATION ET PROCÉDÉ POUR RÉDUIRE LA TENEUR EN ÉLÉMENTS, TELS QUE DU BORE, D'HALOSILANES

Publication

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Application

**EP 08871093 A 20081120**

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Abstract (en)

[origin: CN101486464A] The invention relates to an installation and a method for reducing the content in elements, such as boron, of halosilanes. The invention relates to a method for reducing the content in elements of the third main group of the periodic system, especially in boron- and aluminum-containing compounds of technically pure halosilanes for producing high-purity halosilanes, especially high-purity chlorosilanes. The invention further relates to an installation for carrying out said method. Particularly, the invention relates to a method for lowering content of third main group elements in technically pure halosilanes in order to prepare ultra-pure halosilane, which includes steps of: a) mixing the halosilanes to be purified with triphenylchloromethane to produce complex compound containing these elements; b) separating the complex compound by distillation to obtain ultra-pure halosilane.

IPC 8 full level

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